

# UTC UNISONIC TECHNOLOGIES CO., LTD

# MJE13003D

## NPN SILICON TRANSISTOR

# HIGH VOLTAGE **FAST-SWITCHING NPN** POWER TRANSISTOR

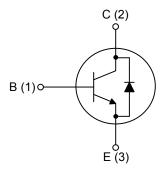
#### **DESCRIPTION**

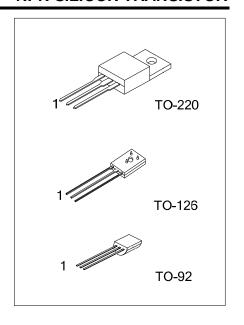
The UTC MJE13003D is a NPN Power Transistor. It is intended to be used in applications requiring medium voltage capability and high switching speeds.

#### **FEATURES**

- \* Fast-Switching And High Voltage Capability
- \* Dynamic Parameters With Low Spread
- \* High Reliability
- \* Integrated Antiparallel Collector-Emitter Diode

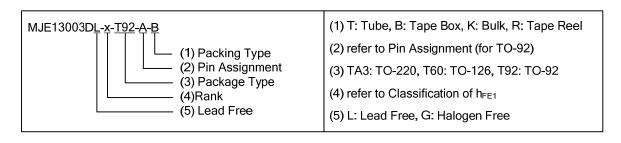
#### INTERNAL SCHEMATIC DIAGRAM





#### ORDERING INFORMATION

Ordering	D. J.	Pin Assignment			5		
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13003DL-x-TA3-T	MJE13003DG-x-TA3-T	TO-220	В	С	E	Tube	
MJE13003DL-x-T60-K	MJE13003DG-x-T60-K	TO-126	В	С	Е	Bulk	
MJE13003DL-x-T92-B	MJE13003DG-x-T92-B	TO-92	В	С	Е	Tape Box	
MJE13003DL-x-T92-K	MJE13003DG-x-T92-K	TO-92	В	С	Е	Bulk	
MJE13003DL-x-T92-R	MJE13003DG-x-T92-R	TO-92	В	С	Е	Tape Reel	
MJE13003DL-x-T92-A-B	MJE13003DG-x-T92-A-B	TO-92	Е	С	В	Tape Box	
MJE13003DL-x-T92-A-K	MJE13003DG-x-T92-A-K	TO-92	Е	С	В	Bulk	
MJE13003DL-x-T92-A-R	MJE13003DG-x-T92-A-R	TO-92	Е	С	В	Tape Reel	



## ■ MARKING INFORMATION

PACKAGE	MARKING
TO-220	UTC MJE13003D ☐ L: Lead Free G: Halogen Free  Lot Code  Data Code  1
TO-126	UTC DDD Data Code  MJE13003D L: Lead Free  1 G: Halogen Free
TO-92	UTC MJE13003D L: Lead Free G: Halogen Free Data Code

#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Collector- Emitter Voltage (V <sub>BE</sub> =0)			$V_{\sf CES}$	700	V
Collector-Emitter Voltage (I <sub>B</sub> =0)			$V_{\sf CEO}$	400	V
Emitter-Base Voltage (I <sub>C</sub> =0, I <sub>B</sub> =0.75A, t <sub>P</sub> <10µS)			$V_{EBO}$	9	V
Collector Current			Ic	1.5	Α
Collector Peak Current (t <sub>P</sub> <5ms)			I <sub>CM</sub>	3	Α
Base Current			I <sub>B</sub>	0.75	Α
Base Peak Current (t <sub>P</sub> <5ms)			I <sub>BM</sub>	1.5	Α
	T <sub>A</sub> =25°C	TO-126		1.4	W
		TO-92		1.1	W
Danna Dia air atian		TO-220	5	2	W
Power Dissipation	T <sub>C</sub> =25°C	TO-126	P <sub>D</sub>	20	W
		TO-92		1.5	W
		TO-220		40	W
Junction Temperature			$T_J$	150	°C
Storage Temperature			T <sub>STG</sub>	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Emitter-Base Breakdown Voltage		$BV_{EBO}$	I <sub>E</sub> =10mA, I <sub>C</sub> =0	9		18	V
Collector-Emitter Sustaining Voltage (Note)		$V_{CEO(SUS)}$	I <sub>C</sub> =10mA, I <sub>B</sub> =0	400			V
Collector Cut-Off Current		I <sub>CES</sub>	V <sub>CE</sub> =700V,V <sub>BE</sub> =0			1	mA
			I <sub>C</sub> =0.5 A, I <sub>B</sub> =0.1 A			0.5	V
Collector-Emitter Saturation	n Voltage (Note)	` ,	I <sub>C</sub> =1 A, I <sub>B</sub> =0.25 A			1	V
			I <sub>C</sub> =1.5 A, I <sub>B</sub> =0.5 A			3	V
Base-Emitter Saturation Voltage (Note)		V <sub>BE(SAT)</sub>	I <sub>C</sub> =0.5 A, I <sub>B</sub> =0.1 A			1	V
			I <sub>C</sub> =1 A, I <sub>B</sub> =0.25 A			1.2	V
DC Current Gain		h <sub>FE1</sub>	I <sub>C</sub> =0.5A, V <sub>CE</sub> =5 V	14		57	
		h <sub>FE2</sub>	I <sub>C</sub> =1 A, V <sub>CE</sub> =5 V	5		30	
	Rise Time	$t_R$	V 405 V I 4 A I 00 A			1	μs
Resistive Load	Storage Time	t <sub>S</sub>	$V_{CC}$ =125 V, $I_{C}$ =1 A, $I_{B1}$ =0.2 A,			4	μs
	Fall Time	$t_{F}$	-I <sub>B2</sub> =-0.2 A, t <sub>P</sub> =25μs			0.7	μs
Inductive Load Storage Time		t <sub>S</sub>	I <sub>C</sub> =1 A, I <sub>B1</sub> =0.2 A,V <sub>BE</sub> =-5 V,		0.8		μs
Diode Forward Voltage		$V_{F}$	L=50mH, V <sub>CLAMP</sub> =300V I <sub>F</sub> =0.5 A			1.5	V

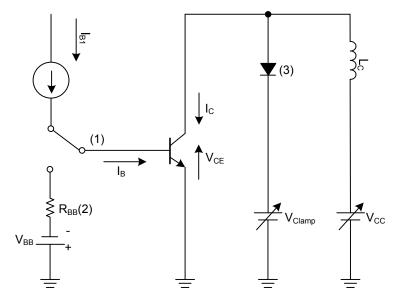
Note: Pulse Test: Pulse duration≤300µs, Duty cycle≤2 %

# ■ CLASSIFICATION OF h<sub>FE1</sub>

RANK	Α	В	С	D	E	F	G	Н
RANGE	14 ~ 22	21 ~ 27	26 ~ 32	31 ~ 37	36 ~ 42	41 ~ 47	46 ~ 52	51 ~ 57

#### ■ TEST CIRCURTS

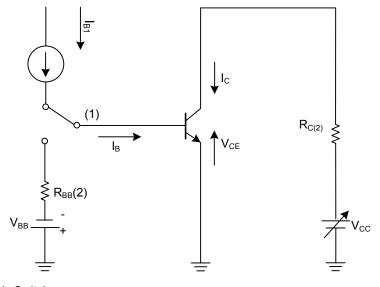
## **Inductive Load Switching Test Circuit**



Notes: 1. Fast Electronic Switch

- 2. Non-Inductive Resistor
- 3. Fast Recovery Rectifier

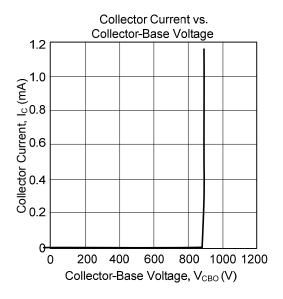
#### **Resistive Load Switching Test Circuit**

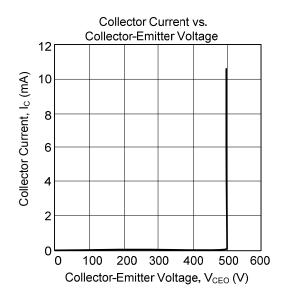


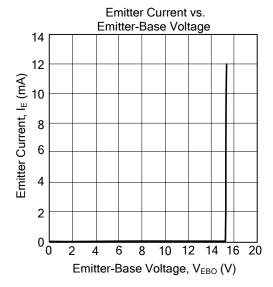
Notes: 1. Fast Electronic Switch

2. Non-Inductive Resistor

#### TYPICAL CHARACTERISTICS







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